


8W/7W 9xxnm High Power Single Emitter Laser Diode on C-mount

SEC8-9xx-01

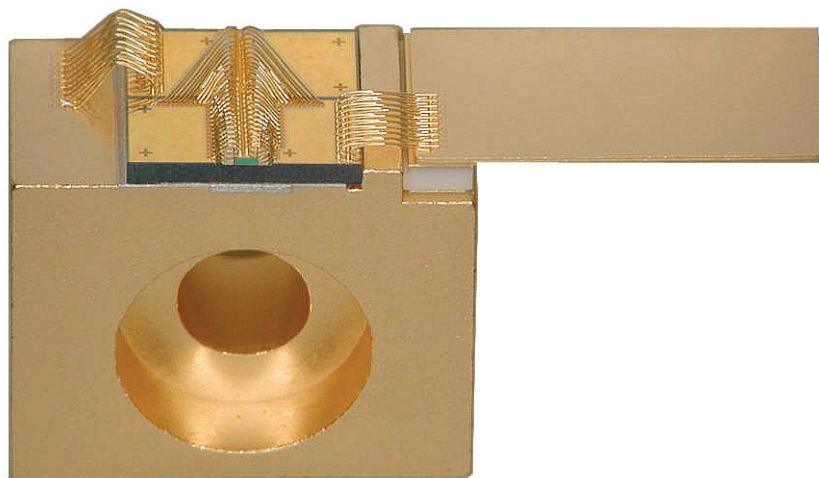
The Bookham SEC8-9xx-01 single emitter laser diode series has been designed to provide the high output power, high coupling efficiency and high reliability required for pumping next generation fiber lasers and for other high power laser diode applications. The proprietary E2 front mirror passivation process, developed at our Zurich site, prevents Catastrophic Optical Damage (COD) to the laser diode facet even at extremely high output powers. The single emitter laser diodes are p-side down mounted on a submount that is attached to a C-mount.

Features:

- 3.6mm x 0.4mm laser diode
- 90µm wide emitter
- Cu C-Mount
- 8W/7W operating power (p-side down mounted)
- Highly reliable single quantum well MBE structure
- Standard wavelength at 915, 940, 960, and 975nm (other available on request)
- RoHS compliant 

Applications:

- Fiber laser pumping
- Material processing
- Printing
- Medical



Characteristics

Parameter	Symbol	Typical	Unit
CW Output Power SEC8-915-01 SEC8-940-01 SEC8-960-01 SEC7-975-01	P_{op915} P_{op940} P_{op960} P_{op975}	8 8 8 7	W
Center Wavelength [1] SEC8-915-01 SEC8-940-01 SEC8-960-01 SEC7-975-01	λ_{c915} λ_{c940} λ_{c960} λ_{c975}	915 ± 10 940 ± 10 960 ± 10 975 ± 10	nm
Spectral Width (FWHM)	$\Delta\lambda$	4	nm
Wavelength Shift with Temperature	$d\lambda_c/dT_{op}$	0.3	nm/°C
Beam Divergence (FWHM) Parallel to Junction Perpendicular to Junction	$\theta_{//}$ θ_{\perp}	8 29	deg
Polarization	–	TE	–
Threshold Current	I_{th}	400	mA
Slope Efficiency	$\eta_D = P_{op} / (I_{op} - I_{th})$	1.0	W/A
Conversion Efficiency	$H = P_{op} / (V_{op} \times I_{op})$	> 50	%
Series Resistance	R_s	0.03	Ω
Operating Current SEC8-915-01 SEC8-940-01 SEC8-960-01 SEC7-975-01	I_{op915} I_{op940} I_{op960} I_{op975}	8.5 8.5 8.5 7.5	A
Operating Voltage	V_{op}	1.9	V
Operating Temperature	T_{op}	25 ± 5	°C

[1] Reduced wavelength window/extended range available on request (900-1070nm).

Chip Dimensions

Parameter	Symbol	Typical	Unit
Chip Width	b	400	μm
Resonator Length	l	3600	μm
Chip Thickness	d	150	μm
Emitter Width	w	90	μm

Package Dimensions (mm)

